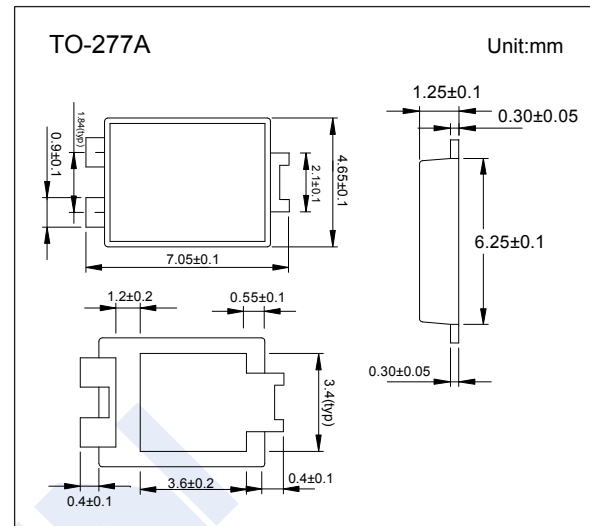
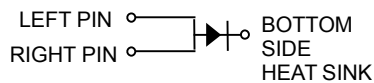


## Schottky Barrier Diodes

## KBR10U60SP5

## ■ Features

- For surface mounted application
- High current capability
- Low forward voltage drop
- Low power loss, high efficiency
- High surge current capability
- High temperature soldering guaranteed:  
260°C/10 seconds at terminals.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Reverse Voltage	VRRM	60	V
RMS Voltage	VRMS	42	
DC blocking Voltage	VDC	60	
Average Forward Rectified Current @ $T_c = 90^\circ\text{C}$	IFAV	10	A
Peak Forward Surge Current @ 8.3ms	IFSM	225	
Thermal Resistance Junction to Case	R <sub>θJC</sub>	12	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature range	T <sub>stg</sub>	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V <sub>R</sub>	I <sub>R</sub> = 100 μA	60			V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 2 A			0.35	
		I <sub>F</sub> = 10 A			0.55	
		I <sub>F</sub> = 2 A, T <sub>a</sub> = 100°C		0.24		
		I <sub>F</sub> = 10 A, T <sub>a</sub> = 100°C		0.39		
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> = 60 V			0.2	mA
		V <sub>R</sub> = 60 V, T <sub>a</sub> = 100°C			20	
Junction capacitance	C <sub>j</sub>	V <sub>R</sub> = 0 V, f = 1 MHz			600	pF

Note.1: Measured at 1.0 MHz and applied reverse voltage of 4.0V DC

## Schottky Barrier Diodes

### KBR10U60SP5

■ Typical Characteristics

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

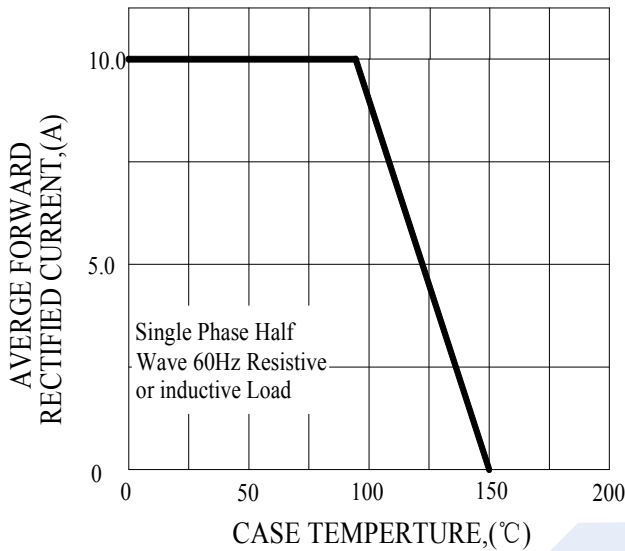


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

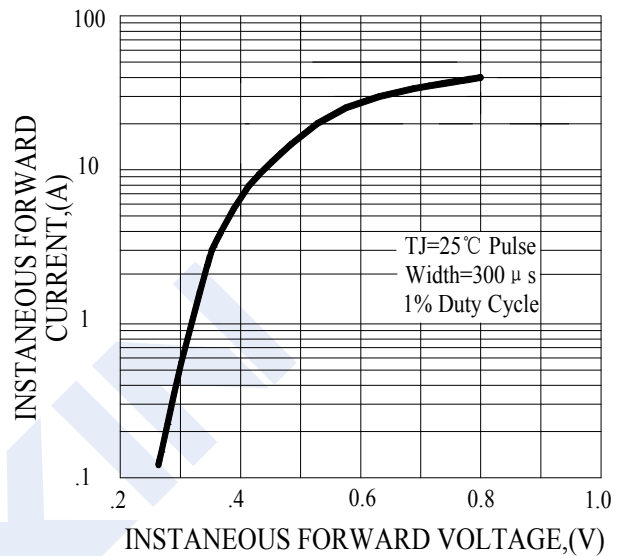


FIG.3-MAXIMUN NON-REPETITIVE FORWARD SURGE CURRENT

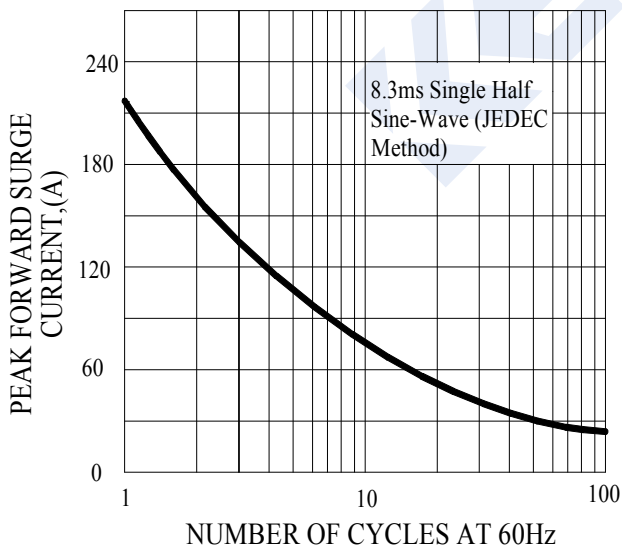


FIG.4-TYPICAL REVERSE CHARACTERISTICS

